

**R18**

Code No: 152AE

**JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD**

**B. Tech I Year II Semester Examinations, January/February - 2024**

**APPLIED PHYSICS**

**(Common to EEE, CSE, IT, CSIT, ITE, CE(SE), CSE(CS), CSE(DS), CSE(N), CSD)**

**Time: 3 Hours**

**Max. Marks: 75**

**Note:** i) Question paper consists of Part A, Part B.

ii) Part A is compulsory, which carries 25 marks. In Part A, answer all questions.

iii) In Part B, Answer any one question from each unit. Each question carries 10 marks and may have a, b as sub questions.

**PART – A**

**(25 Marks)**

- 1.a) Define a matter wave and obtain expression for its wavelength. [2]
- b) Find the energy difference between the ground and first excited state of an electron confined in a potential box of length 1nm. [3]
- c) Draw the V-I characteristics of Zener diode. [2]
- d) Explain the drift and diffusion current in semiconductor [3]
- e) List out applications of direct band gap semiconductors. [2]
- f) Explain the principle of semiconductor laser. [3]
- g) What is pumping and classify the various pumping mechanisms. [2]
- h) Write applications of optical fibers. [3]
- i) Classify the magnetic materials based on the susceptibility. [2]
- j) Write differential form of Maxwell's equations. [3]

**PART - B**

**(50 Marks)**

- 2.a) Derive the wave functions and energy levels associated with an electron confined in a 1-D potential box of length 'L'.
  - b) Explain the Uncertainty principle and its consequences. [6+4]
- OR**
- 3.a) Discuss, how Plancks law explain the radiation of a blackbody.
  - b) Define photoelectric effect and explain Einstein equation for photoelectric effect. [6+4]
- 4.a) Define Hall effect and derive equation for Hall coefficient.
  - b) Explain the junction potential of a PN junction diode subjected to forward and reverse bias. [6+4]
- OR**
- 5.a) Explain the working bipolar junction transistor and mark its current components.
  - b) Write a note on intrinsic and extrinsic semiconductor. [6+4]

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6.a) Explain in detail about radiative and non-radiative recombination process in semiconductors, and for LED materials which type of recombination is being take place.

b) Discuss the different materials used for LED and semiconductor lasers. [6+4]

**OR**

7.a) Discuss the construction and working of a solar cell with its characteristics.

b) Draw the characteristics of PIN diode and explain. [6+4]

8.a) Describe the working of Ruby laser with energy level scheme.

b) Write the applications of lasers. [6+4]

**OR**

9.a) Define numerical aperture of an optical fiber and derive equation for it.

b) Discuss the various sources for the attenuation of signal in optical fibers. [6+4]

10.a) Define internal field in dielectric medium and derive the equation for internal field of a dielectric.

b) Define ferroelectricity and explain the properties of ferroelectric materials. [6+4]

**OR**

11.a) Discuss the domain theory of ferromagnetism.

b) Draw the behavior of ferromagnetic materials in the presence of magnetic field and mention various parts of it. [6+4]

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